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(54) Title: IMPROVED SILICON NITRIDE FILMS AND METHODS

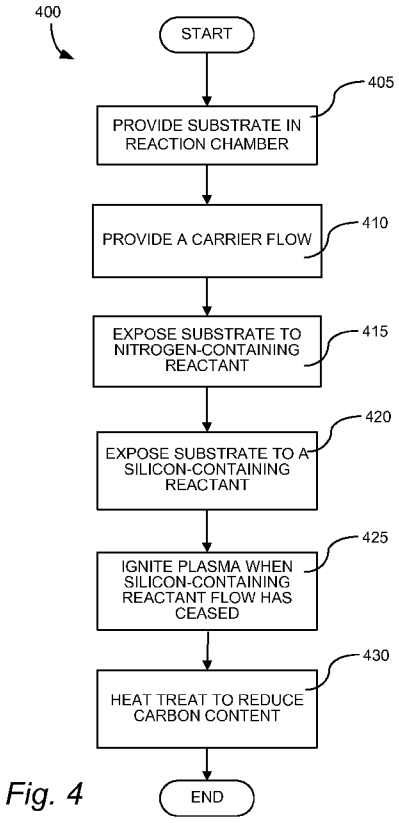


Fig. 4

(57) Abstract: Described are methods of making SiN materials on substrates, particularly SiN thin films on semiconductor substrates. Improved SiN films made by the methods are also included.

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